

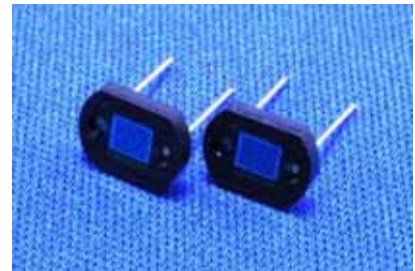
**Silicon Photo Diodes**

**Model No. SD-7BAF**

Optoelectronic device

**Features**

- Sensitive to the visible light only:  $\lambda_p=560\text{nm}$
- Suitable for EE cameras, exposure meters, and others
- High reliability



**Absolute Maximum Ratings**

Ta = 25

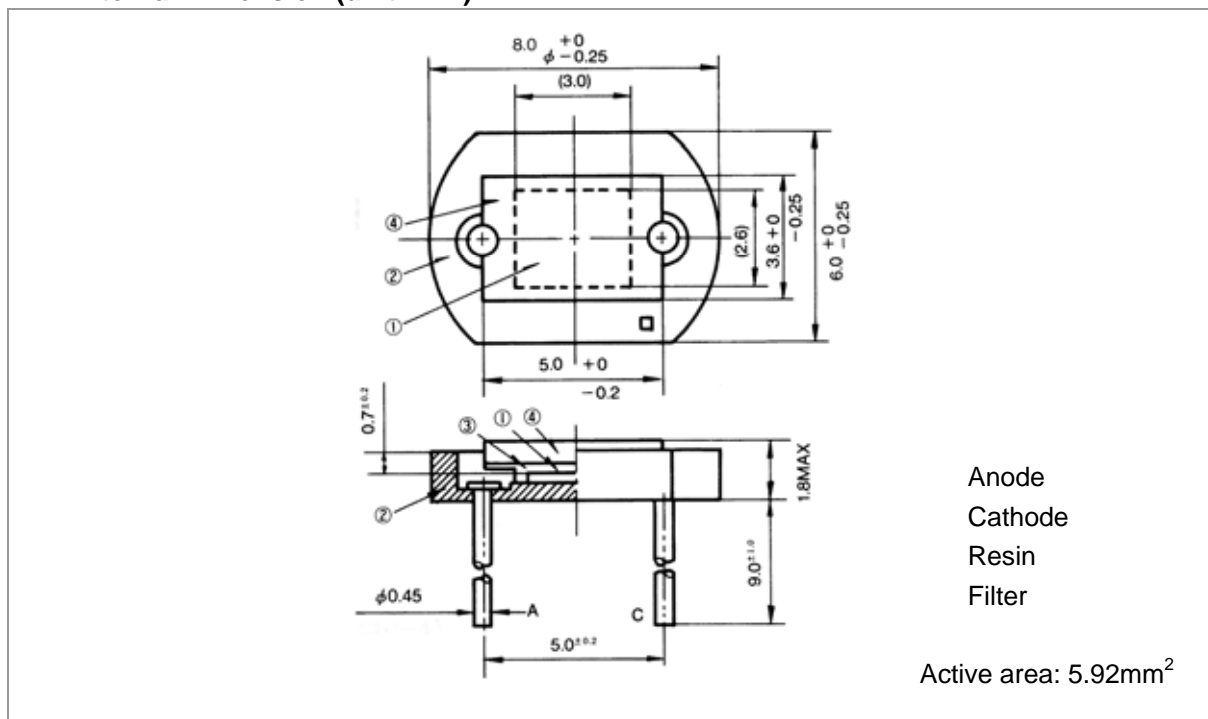
Parameter	Symbol	Value	Unit
DC Reverse Voltage	V <sub>R</sub>	20	V
Operating Temperature	Topr	-20 ~ +60	
Storage Temperature	Tstg	-25 ~ +80	

**Electro-optical Characteristics**

Ta = 25

Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
Sensitive Range		350		730	nm	Equivalent energy
Peak sensitive wavelength	$\lambda_p$		560		nm	Equivalent energy
Short Circuit Current	I <sub>sc</sub>	0.5			$\mu\text{A}$	100Lx
Dark current	I <sub>d</sub>			30	pA	V <sub>R</sub> =1V. RH 65%
Shortcircuit current temp. coefficient	$\tau$		--		%/	100Lx
Dark current temp. coefficient	$\tau$		--		Times/10	V <sub>R</sub> =1V. RH 65%
Terminal capacitance	C <sub>T</sub>		600		pF	V <sub>R</sub> =0V, f=1MHz
Spectral sensitivity	IR		--	--	%	$\lambda=700\text{nm}$ , I <sub>sc</sub> ratio

**External Dimension (unit: mm)**



Package	Ceramic
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